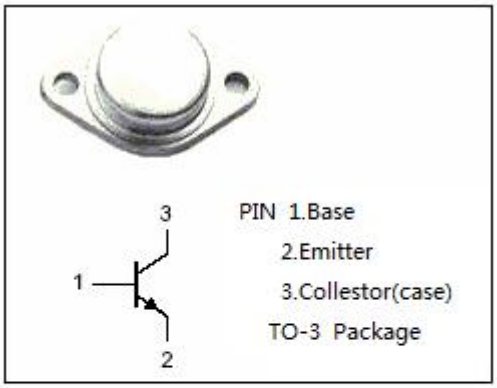
isc Silicon NPN Power Transistor 2SD632

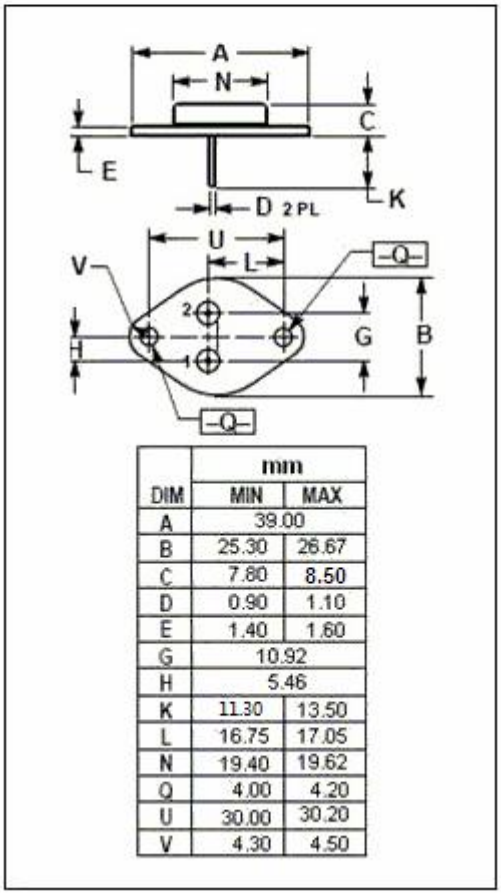
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 300V(Min)
- Excellent Safe Operating Area
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for line operated audio output amplifier,and switching power supply drivers applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	350	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2.5	A
I_{CM}	Collector Current-Peak	5	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 30mA; I_B= 0	300		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.0A; I_B= 0.4A		1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 2.0A; V_{CE}= 10V		1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 350V; I_E= 0		0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 300V; I_B= 0		0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		0.1	mA
h_{FE-1}	DC Current Gain	I_C= 0.5A; V_{CE}= 10V	30	150	
h_{FE-2}	DC Current Gain	I_C= 2A; V_{CE}= 10V	10		
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V	2.5		MHz